

IN THE SPECIFICATION

Please replace the paragraph beginning at page 2, line 14, with the following rewritten paragraph:

Incidentally, adhesion promoter (ADP) processing for supplying an ADP solution to the wafer is performed before the coating solution is supplied to the front surface in order to enhance adhesion of the coating solution on the front surface of the wafer, in which case there is a possibility that the front surface temperature of the wafer changes because of the supply of the ADP solution. An excessive drop in the front surface temperature of the wafer because of the performance of the ADP processing, for example, causes drying of the coating solution not to progress, and thus the large quantity of coating solution supplied to the peripheral edge portion of the wafer is cleared off to the surroundings of the wafer by centrifugal force due to the rotation of the wafer. Consequently, the quantity of the coating solution cleared off increases and hence waste increases. Specially in the edge portion of the wafer, a layer insulating film having a sufficient thickness becomes difficult to form. Conversely, an excessive rise in the front surface temperature of the wafer because of the performance of the ADP processing, for example, causes drying of the coating solution to progress excessively, and thus the coating solution does not spread uniformly to the peripheral edge portion of the wafer. As described above, a change in the front surface temperature of the wafer is not favorable since it causes nonuniformity ununiformity of the layer insulating film. The wafer increases in size these days, and with this increase, harmful effects due to the aforesaid nonuniformity ununiformity of the layer insulating film and an increase in the quantity of the coating solution to be used become a subject of discussion.

Please replace the paragraph beginning at page 13, line 26, with the following rewritten paragraph:

The structure of the second film forming unit 22 (23) will be explained base on FIG. 6. The basic structure thereof is the same as that of the first ~~first~~ film forming unit 20 (21), and a point of difference between them is that a coating solution supply nozzle 65 for supplying a coating solution (a coating solution containing organic macromolecules and the like) as a second processing solution to the front surface of the wafer W in place of the ADP solution supply nozzle 60 is attached to the lid 56. The structure of the second film forming unit 22 (23) except for this point is the same as that of the first film forming unit 20 (21), and the same numerals and symbols will be used to designate the same components as those provided in the first film forming unit 20 (21) out of components of the second film forming unit 22 (23), so that the repetition of explanation will be omitted. It should be mentioned that the coating solution is a liquid which is a raw material for forming a layer insulating film on the wafer W.

Please replace the paragraph beginning at page 21, line 15, with the following rewritten paragraph:

Thereafter, the wafer W is carried into the first film forming unit 20 (21), vacuum-sucked by the spin chuck 52, and housed in the cup 51. The ADP solution is supplied from ~~from~~ the ADP solution supply nozzle 60, and the wafer W is rotated by the spin chuck 52. The ADP solution is spread over the entire front surface of the wafer W by centrifugal force due to the rotation of the wafer W (S2). Thus, ADP processing is completed.

Please replace the paragraph beginning at page 27, line 23, with the following rewritten paragraph:

Next, experiments of the present invention are performed. The film forming system explained in FIG. 1 to FIG. 7 is prepared, and a coating solution film is formed on the wafer. The relationship between the front surface temperature of the wafer and the uniformity of the coating solution film is examined. In this case, both a conventional film forming method and the film forming method of the present invention are put into practice, and the results thereof are compared. An object of experiments is a wafer with a diameter of 200 millimeters, the components of the ADP solution contain propylene glycol monomethyl ether (PGME) and propylene glycol methyl ether acetate (PMA) PGME and PMA, and the components of the coating solution contain cyclohexane.